

Memristive Devices and Circuits for Computing, Memory, and Neuromorphic Applications

by

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Abstract

A memristor, *memory resistor*, is a two-terminal nanodevice that can be made as thin as a single-atom-thick that has become of tremendous interest for its potential to revolutionise electronics, computing, computer architectures, and neuromorphic engineering. This thesis encompasses two major parts containing original contributions, (**Part I**) modelling and fabrication, and (**Part II**) circuit application and computing. Each part contains three chapters. The fundamentals necessary for understanding the main idea of each chapter are provided therein. A background chapter revolving around memristors and memristive devices is given. A system overview links the two parts together. A brief description of the two parts is as follows:

Part I—modelling and fabrication is relevant to modelling and fabrication of memristors. A basic modelling approach following the early modelling by Hewlett-Packard is presented and tested with several simple circuits. Memristor fabrication process and materials are discussed and two different fabrication runs along with initial measurement results are presented. SPICE modelling for two memristive devices, (i) the memristor and (ii) the complementary resistive switch are also provided.

Part II—nanocrossbar array and memristive-based memory and computing provides an analytical approach for crossbar arrays based on memristive devices. Proposed designs for memristor-based content addressable memories and their analysis are given. This part provides a binary/ternary content addressable memory structure based on a new complementary resistive switch. A number of fundamental building blocks for analogue and digital computing are also presented in this section. The observation of implementing a learning process based on a pair of spikes is also shown and an extension of such a process to a relatively large scale structure based on SPICE simulation is reported.

In addition to these original contributions, the thesis offers an introductory background on memristors, in the area of materials and applications. The thesis also provides a system overview of the targeted system (a CMOS-memristor imager system),

which provides a the link between the two parts of the thesis. In addition to the original contributions in the area of modelling and characterisation, an overview on the understanding of the memristor element via the quasistatic expansion of Maxwell's equations is discussed.

Statement of Originality

This work contains no material that has been accepted for the award of any other degree or diploma in any university or other tertiary institution to Omid Kavehei and, to the best of my knowledge and belief, contains no material previously published or written by another person, except where due reference has been made in the text.

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December 28, 2011

Signed

Date

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The research presented in this thesis has been carried out in the School of Electrical and Electronic Engineering at the University of Adelaide. The path towards this thesis spans three years of a multidisciplinary research covering nanoelectronics, materials engineering, and circuit design. It has been an honour and great privilege to be the first Ph.D. student on the emerging topic of memristive devices and systems in Australia at a university with a solid and strong background in microelectronics. From the outset, many people have been involved and have contributed to the presented ideas and understanding gained. I gratefully acknowledge those who have helped along the way and influenced the formation of the understanding and the approach to representation of materials presented in this thesis.

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O. Kavehei

Conventions

Typesetting This thesis is typeset using the L^AT_EX2e software. T_EXnicCenter is used as an effective interface to L^AT_EX.

Referencing The Harvard style is used for referencing and citation in this thesis.

Spelling Australian English spelling is adopted, as defined by the Macquarie English Dictionary (Delbridge 2001).

System of units The units comply with the international system of units recommended in an Australian Standard: AS ISO 1000—1998 (Standards Australia Committee ME/71, Quantities, Units and Conversions 1998).

Physical constants The physical constants comply with a recommendation by the Committee on Data for Science and Technology: CODATA (Mohr and Taylor 2005).

Publications

Journal publications

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